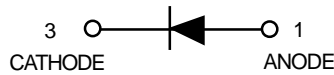


High-Speed Switching Diode



MMBD914LT1



CASE 318-08, STYLE 8
SOT- 23 (TO-236AB)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	100	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board ⁽¹⁾ $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, ⁽²⁾ $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	°C

DEVICE MARKING

MMBD914LT1 = 5D

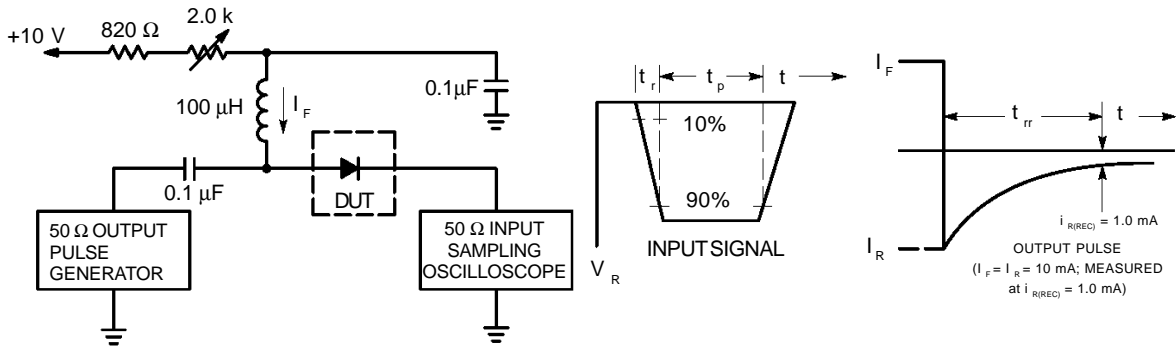
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_R = 100 \mu\text{Adc}$)	$V_{(BR)}$	100	—	Vdc
Reverse Voltage Leakage Current ($V_R = 20 \text{Vdc}$)	I_R	—	25	nAdc
($V_R = 75 \text{Vdc}$)		—	5.0	μAdc
Diode Capacitance ($V_R = 0, f = 1.0 \text{MHz}$)	C_T	—	4.0	pF
Forward Voltage ($I_F = 10 \text{mAdc}$)	V_F	—	1.0	Vdc
Reverse Recovery Time ($I_F = I_R = 10 \text{mAdc}$) (Figure 1)	t_{rr}	—	4.0	ns

1. FR-5 = 1.0 x 0.75 x 0.062 in.

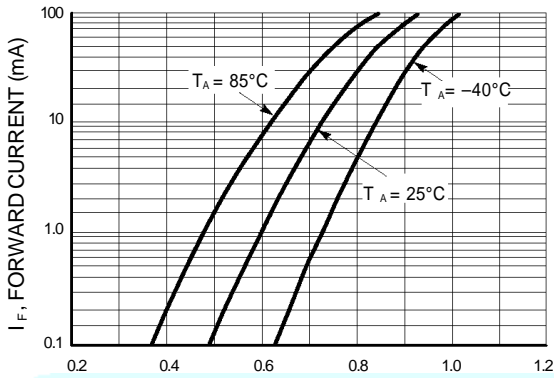
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

MMBD914LT1



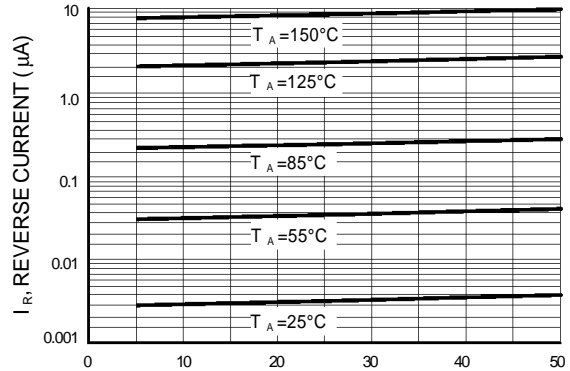
- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10mA.
 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10mA.
 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit



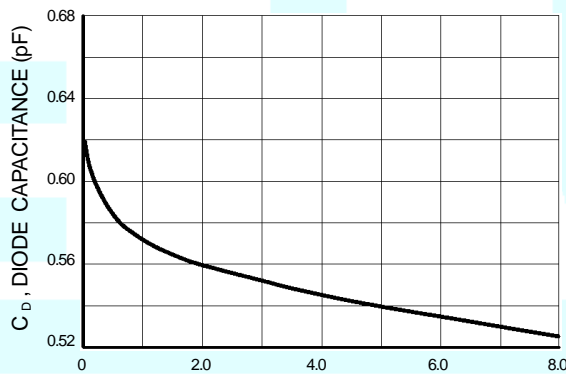
V_F , FORWARD VOLTAGE (VOLTS)

Figure 2. Forward Voltage



V_R , REVERSE VOLTAGE (VOLTS)

Figure 3. Leakage Current



V_R , REVERSE VOLTAGE (VOLTS)

Figure 4. Capacitance